

ABSTRACT OF THE DISCLOSURE

The present invention is to carry out stable doping and to prevent the drastic pressure change in a treatment chamber by reducing degasification of resist during adding impurities. In the present invention, the stability of the impurity ion injection
5 can be ensured by reducing degasification of resist by reducing the area (resist area proportion, that is, the ratio of the area of resist to the whole area of a substrate) of resist pattern which is used depending on the conditions such as acceleration voltage or current density of a doping process.